

| | | |
|--|----------------------|---------------------------------|
| Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(Use as many sheets as necessary)</i> | Complete if Known | |
| | Application Number | 10/081,818 |
| | Filing Date | February 20, 2002 |
| | First Named Inventor | Eldridge, Jerome |
| | Group Art Unit | 2818 |
| | Examiner Name | Ho, Tu-Tu |
| Sheet 1 of 1 | | Attorney Docket No: 1303.045US1 |

| US PATENT DOCUMENTS | | | | |
|---------------------|---------------------|------------------|---|----------------------------|
| Examiner Initial * | USP Document Number | Publication Date | Name of Patentee or Applicant of cited Document | Filing Date if Appropriate |
| TH | US-20020024083A1 | 02/28/2002 | Noble, W. P., et al. | 02/26/1999 |
| ↓ | US-20060186458A1 | 08/24/2006 | Forbes, L., et al. | 02/23/2005 |
| | US-4,510,584 | 04/09/1985 | Dias, D. R., et al. | 12/29/1982 |
| | US-4,545,035 | 10/01/1985 | Guterman, D. C., et al. | 07/20/1982 |
| | US-4,665,417 | 05/12/1987 | Lam, C. h. | 04/23/1986 |
| ↓ | US-5,057,448 | 10/15/1991 | Kuroda, K. | 02/10/1989 |
| | US-5,331,188 | 07/19/1994 | Acovic, A., et al. | 02/25/1992 |
| TH | US-7,112,841 | 09/26/2006 | Eldridge, J. M., et al. | 02/18/2004 |

| FOREIGN PATENT DOCUMENTS | | | | |
|--------------------------|---------------------|------------------|---|-----|
| Examiner Initials * | Foreign Document No | Publication Date | Name of Patentee or Applicant of cited Document | T * |

| OTHER DOCUMENTS – NON PATENT LITERATURE DOCUMENTS | | | | |
|---|----------------------|---|--|-----|
| Examiner Initials * | Cite No ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | | T * |
| TH | | "ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS", <u>US Application Serial No 10/379470 (1303.090US1) filed March 4, 2003,</u> | | |
| ↓ | | "COBALT TITANIUM OXIDE DIELECTRIC FILMS", <u>US Application Serial No. 11/216958 (Attorney Docket No 1303.150US1), filed August 31, 2005,</u> | | |
| | | "MAGNESIUM TITANIUM OXIDE FILMS", <u>US Application Serial No 11/89075 (Attorney Docket No. 1303.148US1) filed July 25, 2005,</u> | | |
| | | AHN, "ATOMIC LAYER DEPOSITED DIELECTRIC LAYERS", <u>US Application Serial No 10/379470 (1303.090US1), filed 03/04/2003</u> | | |
| | | AHN, "CONDUCTIVE NANOPARTICLES", <u>US Application Serial No 11/197,184 (Attmy Docket No.303.904US1), filed August 4, 2005,</u> | | |
| | | AHN, "IRIDIUM / ZIRCONIUM OXIDE STRUCTURE", <u>US Application Serial No 11/152759 (Attmy Docket No. 1303.144US1) filed June 14, 2005,</u> | | |
| | | AHN, KIE Y., "LANTHANIDE YTTRIUM ALUMINUM OXIDE DIELECTRIC FILMS", <u>U.S. Application Serial No. 11/297,567, filed December 8, 2005 (Attorney Docket 1303.157US1), 05-0711,</u> | | |
| ↓ | | AHN, "LANTHANUM ALUMINUM OXYNITRIDE DIELECTRIC FILMS", <u>US Application Serial No 11/216474 (Attorney Docket No. 1303.152US1) filed August 31, 2005,</u> | | |
| TH | | GEALY, et al., "GRADED DIELECTRIC LAYERS", <u>US Application Serial No 11/216,542 (Attmy Docket No 303.903US1) filed August 30, 2005,</u> | | |

EXAMINER

/Tu Tu Ho/ (12/15/2006)

DATE CONSIDERED 12/15/2006

PTO/28906A(10-01)

Approved for use through 10/31/2002. OMB 051-0031
US Patent & Trademark Office U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)

Complete if Known

Application Number 10/081,818

Filing Date February 20, 2002

First Named Inventor Eldridge, Jerome

Group Art Unit 2818

Examiner Name Ho, Tu-Tu

FAX RECEIVED

FEB 05 2007

OFFICE OF PETITIONS

Sheet 1 of 1

Attorney Docket No: 1303.045US1

US PATENT DOCUMENTS

| Examiner Initial * | USP Document Number | Publication Date | Name of Patentee or Applicant of cited Document | Filing Date If Appropriate |
|--------------------|---------------------|------------------|---|----------------------------|
| TH | US-20030134475A1 | 07/17/2003 | Hofmann, F., et al. | 01/28/2003 |
| | US-20040207038A1 | 10/21/2004 | Hofmann, F., et al. | 05/17/2004 |
| | US-20060278917A1 | 12/14/2006 | Forbes, L., et al. | 08/22/2006 |
| | US-5,739,567 | 04/14/1998 | Wong, Chun Chiu D. | 11/08/1994 |
| | 5,768,192 | 06/16/1998 | Eitan | 07/23/1996 |
| | US-5,969,383 | 10/19/1999 | Chang, Kuo-Tung, et al. | 06/16/1997 |
| | US-6,087,222 | 07/11/2000 | Jung Lin, C, et al. | 03/05/1998 |
| | US-6,118,159 | 09/12/2000 | Willer, J., et al. | 02/26/1999 |
| | US-6,157,061 | 12/05/2000 | Kawata, M. | 08/27/1998 |
| | US-6,191,459 | 02/20/2001 | Hofmann, Franz, et al. | 01/08/1997 |
| | US-6,204,529 | 03/20/2001 | Lung, Hsing Lan, et al. | 08/27/1999 |
| | US-6,335,554 | 01/01/2002 | Yoshikawa, Kuniyoshi | 03/07/2000 |
| | US-6,378,312 | 04/23/2002 | Yu, A. S. | 03/26/2001 |
| | US-6,396,745 | 05/28/2002 | Hong, G., et al. | 02/15/2001 |
| | US-7,154,138 | 12/26/2006 | Hofmann, Franz, et al. | 06/20/2002 |
| | US-7,166,886 | 01/23/2007 | Forbes, L. | 02/20/2004 |

FOREIGN PATENT DOCUMENTS

| Examiner Initial * | Foreign Document No | Publication Date | Name of Patentee or Applicant of cited Document | T* |
|--------------------|---------------------|------------------|---|----|
|--------------------|---------------------|------------------|---|----|

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

| Examiner Initials * | Cite No * | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T* |
|---------------------|-----------|---|----|
| TH | | EITAN, BOAZ, et al., "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell", IEEE Electron Device Letters, 21(11), (November 2000), 543-545 | |

EXAMINER

/Tu Tu Ho/ (02/28/2007)

DATE CONSIDERED

02/28/2007

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 608. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. * Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

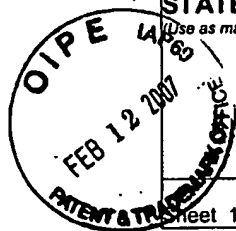
(Use as many sheets as necessary)

Complete if Known

| | |
|----------------------|-------------------|
| Application Number | 10/081,818 |
| Filing Date | February 20, 2002 |
| First Named Inventor | Eldridge, Jerome |
| Group Art Unit | 2818 |
| Examiner Name | Ho, Tu-Tu |

Attorney Docket No: 1303.045US1

Sheet 1 of 1

**US PATENT DOCUMENTS**

| Examiner Initial * | USP Document Number | Publication Date | Name of Patentee or Applicant of cited Document | Filing Date If Appropriate |
|--------------------|---------------------|------------------|---|----------------------------|
| TH | US-5,042,011 | 08/20/1991 | Casper, Stephen L., et al. | 05/22/1989 |
| | US-5,280,205 | 06/18/1994 | Green, Robert S., et al. | 04/16/1992 |
| | US-5,497,494 | 03/05/1996 | Combs, James L., et al. | 07/23/1993 |
| | US-5,619,642 | 04/08/1997 | Nielsen, Michael E., et al. | 12/23/1994 |
| | US-5,627,785 | 05/06/1997 | Gilliam, Gary R., et al. | 03/15/1996 |
| | US-5,691,230 | 11/25/1997 | Forbes, Leonard | 09/04/1996 |
| | US-6,134,175 | 10/17/2000 | Forbes, Leonard , et al. | 08/04/1998 |
| | US-6,135,175 | 10/24/2000 | Gaudreault, Pierre , et al. | 10/19/1998 |
| | US-6,153,468 | 11/28/2000 | Forbes, Leonard , et al. | 05/17/1999 |
| | US-6,249,020 | 06/19/2001 | Forbes, Leonard , et al. | 08/27/1998 |
| | US-6,307,775 | 10/23/2001 | Forbes, Leonard , et al. | 08/27/1998 |
| | US-6,323,844 | 11/27/2001 | Yeh, Fu-Kuo , et al. | 08/11/1997 |
| | US-6,351,411 | 02/26/2002 | Forbes, Leonard , et al. | 06/12/2001 |

FOREIGN PATENT DOCUMENTS

| Examiner Initials* | Foreign Document No | Publication Date | Name of Patentee or Applicant of cited Document | T ² |
|--------------------|---------------------|------------------|---|----------------|
|--------------------|---------------------|------------------|---|----------------|

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

| Examiner Initials* | Cite No. ¹ | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T ² |
|--------------------|-----------------------|---|----------------|
| TH | | AHN, KIE Y., et al., "MAGNESIUM TITANIUM OXIDE FILMS", U.S. Application Serial No. 11/189,075, filed July 25, 2005 (Attorney Docket 1303.148US1) | |
| TH | | HODGES, D. A., et al., "Analysis and Design of Digital Integrated Circuits", McGraw-Hill Book Company, 2nd Edition, (1988), 394-396 | |
| TH | | HODGES, D. A., "Analysis and Design of Digital Integrated Circuits, 2nd Edition", McGraw-Hill Publishing, New York, (1988), 354-357 | |
| TH | | SHI, YING , et al., "Tunneling leakage current in ultrathin (<4 nm) nitride/oxide stack dielectrics", IEEE Electron Device Letters, 19(10), (1998), 388-390 | |

EXAMINER

/Tu Tu Ho/ (02/28/2007)

DATE CONSIDERED

02/28/2007

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.



N 10/081,818

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Jerome M. Eldridge et al. Examiner: Tu-Tu V. Ho
Serial No.: 10/081,818 Group Art Unit: 2818
Filed: February 20, 2002 Docket: 1303.045US1
Title: ATOMIC LAYER DEPOSITION OF METAL OXIDE AND/OR LOW
ASYMMETRICAL TUNNEL BARRIER INTERPOLY INSULATORS

COMMUNICATION CONCERNING RELATED APPLICATIONS

MS Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Noted, Feb. 07 Applicants would like to bring to the Examiner's attention the following related applications in the above-identified patent application:

| | <u>Serial/Patent No.</u> | <u>Filing Date/Issue Date</u> | <u>Attorney Docket</u> | <u>Title</u> |
|----|--------------------------|-------------------------------|------------------------|---|
| TH | 11508090 | August 22, 2006 | 1303.024US4 | FLOATING GATE STRUCTURES |
| TH | 11590363 | October 31, 2006 | 1303.014US3 | FLASH MEMORY WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS |
| TH | 11565826 | December 1, 2006 | 1303.141US2 | HAFNIUM TITANIUM OXIDE FILMS |
| TH | 11619080 | January 2, 2007 | 1303.027US4 | IN SERVICE PROGRAMMABLE LOGIC ARRAYS WITH LOW TUNNEL BARRIER INTERPOLY INSULATORS |

Continuations and divisionals may be later filed on the cases listed above, or cited to the Examiner in any previous Communication Concerning Related Applications. Applicants request that the Examiner review all continuations and divisionals of the above-listed or previously-cited patent applications before allowing the claims of the present patent application.

Respectfully submitted,

JEROME M. ELDRIDGE ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
P.O. Box 2938
Minneapolis, MN 55402
(612) 349-9587

Date 8 Feb '07

By [Signature]
Timothy B. Clise
Reg. No. 40,957

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: MS Amendment, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 8 day of February, 2007.

[Signature]
Name

[Signature]
Signature